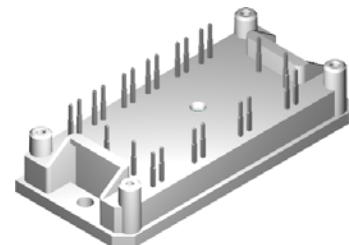
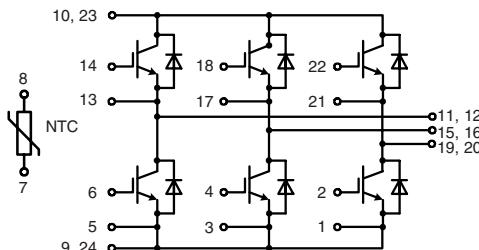


IGBT Module**Sixpack**

Short Circuit SOA Capability

Square RBSOA

I_{C25} = 51 A
 V_{CES} = 1200 V
 $V_{CE(sat)\text{ typ.}}$ = 2.4 V

**IGBTs**

Symbol	Conditions	Maximum Ratings		
V_{CES}	$T_{VJ} = 25^\circ\text{C}$ to 150°C	1200		V
V_{GES}		± 20		V
I_{C25}	$T_C = 25^\circ\text{C}$	51		A
I_{C80}	$T_C = 80^\circ\text{C}$	36		A
I_{CM}	$V_{GE} = \pm 15 \text{ V}$; $R_G = 39 \Omega$; $T_{VJ} = 125^\circ\text{C}$	70		A
V_{CEK}	RBSOA; clamped inductive load; $L = 100 \mu\text{H}$		V_{CES}	
t_{sc}	$V_{CE} = 900 \text{ V}$; $V_{GE} = \pm 15 \text{ V}$; $R_G = 39 \Omega$; $T_{VJ} = 125^\circ\text{C}$ SCSOA; non-repetitive	10		μs
P_{tot}	$T_C = 25^\circ\text{C}$	210		W

Symbol	Conditions	Characteristic Values		
		($T_{VJ} = 25^\circ\text{C}$, unless otherwise specified)		
$V_{CE(sat)}$	$I_C = 35 \text{ A}$; $V_{GE} = 15 \text{ V}$; $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	2.4	2.9	V
		2.8		V
$V_{GE(th)}$	$I_C = 1 \text{ mA}$; $V_{GE} = V_{CE}$	4.5		V
I_{CES}	$V_{CE} = V_{CES}$; $V_{GE} = 0 \text{ V}$; $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$		0.3	mA
			1.2	mA
I_{GES}	$V_{CE} = 0 \text{ V}$; $V_{GE} = \pm 20 \text{ V}$		200	nA
$t_{d(on)}$ t_r $t_{d(off)}$ t_f E_{on} E_{off}	Inductive load, $T_{VJ} = 125^\circ\text{C}$ $V_{CE} = 600 \text{ V}$; $I_C = 35 \text{ A}$ $V_{GE} = \pm 15 \text{ V}$; $R_G = 39 \Omega$	90		ns
		50		ns
		440		ns
		50		ns
		5.4		mJ
		2.6		mJ
C_{ies} Q_{Gon}	$V_{CE} = 25 \text{ V}$; $V_{GE} = 0 \text{ V}$; $f = 1 \text{ MHz}$ $V_{CE} = 600 \text{ V}$; $V_{GE} = 15 \text{ V}$; $I_C = 35 \text{ A}$	2000		pF
		150		nC
R_{thJC} R_{thCH}	(per IGBT)		0.6	K/W
			0.2	K/W

IXYS reserves the right to change limits, test conditions and dimensions.

查询"MWI50-12E6K"供应商

Diodes

Symbol	Conditions	Maximum Ratings		
I_{F25}	$T_C = 25^\circ C$	49	A	
I_{F80}	$T_C = 80^\circ C$	32	A	

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
V_F	$I_F = 35 A; V_{GE} = 0 V; T_{VJ} = 25^\circ C$ $T_{VJ} = 125^\circ C$	2.6	2.9	V
		1.8		V
I_{RM} t_{rr}	$\left. \begin{array}{l} I_F = 35 A; dI_F/dt = -600 A/\mu s; T_{VJ} = 100^\circ C \\ V_R = 600 V; V_{GE} = 0 V \end{array} \right\}$	35		A
		150		ns
R_{thJC} R_{thCH}	(per Diode)	0.3	0.9	K/W
				K/W

Temperature Sensor NTC

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
R_{25}	$T = 25^\circ C$	4.45	4.7	5.0
$B_{25/85}$			3510	kΩ
				K

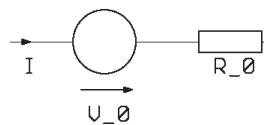
Module

Symbol	Conditions	Maximum Ratings		
T_{VJ}	operating	-40...+125		°C
T_{VJM}		-40...+150		°C
T_{stg}		-40...+125		°C
V_{ISOL}	$I_{ISOL} \leq 1 mA; 50/60 Hz$	2500		V~
M_d	Mounting torque (M4)	2.0 - 2.2		Nm

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
d_s	Creepage distance on surface	12.7		mm
d_A	Strike distance in air	12.7		mm
Weight		40		g

Equivalent Circuits for Simulation

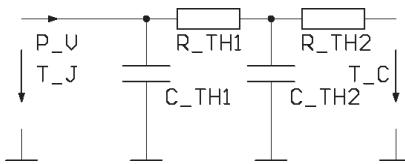
Conduction



IGBT (typ. at $V_{GE} = 15 V; T_J = 125^\circ C$)
 $V_o = 1.0 V; R_o = 44 m\Omega$

Free Wheeling Diode (typ. at $T_J = 125^\circ C$)
 $V_o = 1.5 V; R_o = 14 m\Omega$

Thermal Response



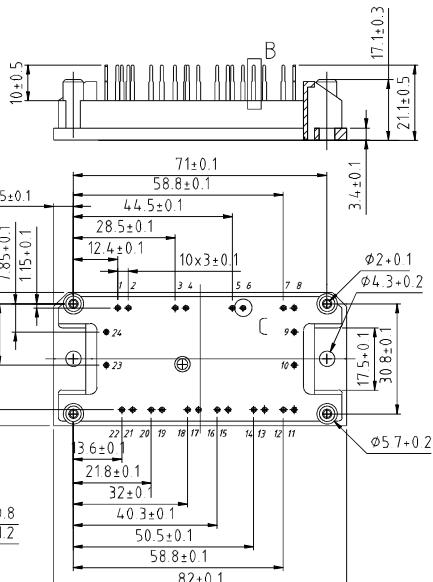
IGBT (typ.)

$C_{th1} = tbd \text{ J/K}; R_{th1} = tbd \text{ K/W}$
 $C_{th2} = tbd \text{ J/K}; R_{th2} = tbd \text{ K/W}$

Free Wheeling Diode (typ.)

$C_{th1} = tbd \text{ J/K}; R_{th1} = tbd \text{ K/W}$
 $C_{th2} = tbd \text{ J/K}; R_{th2} = tbd \text{ K/W}$

Dimensions in mm (1 mm = 0.0394")



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